Radiation Report

TPS7H6003-SP Single-Event Effects (SEE) Report

TEXAS INSTRUMENTS

ABSTRACT

The purpose of this study is to characterize the single-event effects (SEE) performance due to heavy-ion irradiation of the TPS7H6003-SP. Heavy-ions with LET_{EFF} of 48, 65, and 75 MeV × cm^2 / mg was used to irradiate four production devices. Flux of ≈ 10^5 ions / cm^2 ·s and fluence of ≈ 10^7 ions / cm^2 per run were used for the characterization. The results demonstrate the performance of the TPS7H6003-SP under SEL and SEB/SEGR conditions at T = 125°C and T = 25°C respectively. SET transients performance for output pulse width excursions ≥ |20%| from the nominal width and positive and negative edge transients on HO and LO are presented and discussed.

Table of Contents

List of Figures

List of Tables

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1 Introduction

The TPS7H6003-SP is a 200-V radiation-hardness-assured (RHA) Gallium Nitride (GaN) Field Effect Transistor (FET) gate driver designed for high frequency, high efficiency applications. The driver features:

- Adjustable dead time (PWM mode)
- Approximately 30-ns propagation delay
- Approximately 5.5-ns high-side and low-side matching
- High-side/low-side 5-V LDOs independent of supply voltage
- Two control input modes: Independent Input Mode (IIM) and PWM
  - IIM allows for outputs to be controlled by dedicated input
  - PWM allows for two complementary outputs signals to be generated from single input with resistor programmable dead-time

In IIM mode the user also has the ability to enable or disable the turn-on of both outputs when both inputs are on simultaneously (interlock protection). This gives the driver the ability to be used in multiple converter configurations.

The device is offered in a 48-pin ceramic package. General device information and test conditions are listed in Table 1-1. For more detailed technical specifications, user guides, and application notes, see TPS7H6003-SP product page.

Table 1-1. Overview Information

DESCRIPTION(1)	DEVICE INFORMATION
TI part number	TPS7H6003-SP
Orderable number	5962R2220101VXC
Device function	200-V half-bridge eGaN gate driver
Technology	LBC7 (Linear BiCMOS 7)
Exposure facility	Radiation Effects Facility, Cyclotron Institute, Texas A&M University (15 MeV / nucleon)
Heavy ion fluence per run	9.97×10^6 – 1.00×10^7 ions / cm^2
Irradiation temperature	25°C (for SEB/SEGR testing), 25°C (for SET testing), and 125°C (for SEL testing)

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2 Single-Event Effects (SEE)

SEE testing was performed on an evaluation board designed for testing the TPS7H6003-SP under heavy-ion radiation. The board was powered up in different input and output conditions at Texas A&M University to cover the spectrum of destructive SEE (DSEE) and Single-Event Transients (SET). The devices were tested at the TAMU Cyclotron Radiation Effects Facility using a superconducting cyclotron and an advanced electron cyclotron resonance (ECR) ion source. DSEE testing included Single-Event Latch-up (SEL), Single-Event Burnout (SEB), and Single-Event Gate Rupture (SEGR). In mixed technologies such as the BiCMOS process used on the TPS7H6003-SP, the CMOS circuitry introduces a potential for SEL susceptibility.

SEL can occur if excess current injection caused by the passage of an energetic ion is high enough to trigger the formation of a parasitic cross-coupled PNP and NPN bipolar structure (formed between the p-sub and n-well and n+ and p+ contacts) [1,2]. The parasitic bipolar structure initiated by a single-event creates a high-conductance path (inducing a steady-state current that is typically orders-of-magnitude higher than the normal operating current) between power and ground that persists (is “latched”) until power is removed, the device is reset, or until the device is destroyed by the high-current state. The TPS7H6003-SP was tested for SEL at the maximum recommended input voltage (V_{IN}) of 14-V and the maximum recommended boot voltage (V_{BOOT}) of 14-V. The ASW (High-Side Driver Signal Return) was set to 150-V. Three different operation modes were tested during SEL testing. The first mode was PWM mode with the EN (HI) and PWM (LI) inputs in the following configuration:

- EN/HI:
  - 14-V DC signal (SEL)
- PWM/LI:
  - 14-V square wave switching at 500 kHz, 1 MHz, and 2 MHz (SEL)

The second and third modes of operation were IIM_{EN} (where the optional interlock protection is enabled) and IIM_{DIS} (where the optional interlock protection is disabled) mode (for the IIM modes there are static (IIM_{ST}) and switching (IIM_{SW}) cases) in which EN (HI) and PWM (LI) were configured in the following manner (both cases were tested under the same conditions):

- Case 1 - EN/HI = 0 V, PWM/LI = 14 V (Static SEL)
- Case 2 - EN/HI = 14 V, PWM/LI = 0 V (Static SEL)
- Case 3- EN/HI and PWM/LI = 14 V square wave switching at 500-kHz offset by 180° (Switching SEL)

During testing of the four devices, the TPS7H6003-SP did not exhibit any SEL with heavy-ions with LET_{EFF} = 75 MeV × cm^2 / mg at flux of approximately 10^5 ions / cm^2 × s, fluence of approximately 10^7 ions / cm^2, and a die temperature of 125°C.

The primary concern for SEB and SEGR was the power LDMOS of this device. Because of this, SEB/SEGR was evaluated up to the maximum V_{IN} and V_{BOOT} in both IIM and PWM mode. In IIM mode the TPS7H6003-SP was also tested in the “Off” case in which both EN/HI and PWM/LI = 0 V to determine if either of the outputs incorrectly turned on when the outputs must not have during heavy-ion radiation. Because it has been shown that the MOSFET susceptibility to burnout decrements with temperature [5], the device was evaluated while operating under room temperatures. The specific test conditions the device was tested are as follows:

PWM Mode:

- EN/HI:
  - 14-V DC signal (SEB_{ON})
  - 0-V DC signal (SEB_{OFF})
- PWM/LI:
  - 14-V Square Wave switching at 500-kHz, 1 MHz, and 2 MHz (SEB_{ON})
  - 0-V DC signal (SEB_{OFF})

IIM Modes:

- Case 1- EN/HI = 0-V, PWM/LI = 14 V (Static SEB_{ON})
- Case 2 - EN/HI = 14-V, PWM/LI = 0 V (Static SEB_{ON})
- Case 3 - EN/HI = 0-V, PWM/LI = 0 V (SEB_{OFF})
- Case 4 - EN/HI & PWM/LI = 14-V square wave switching at 500-kHz offset by 180° (Switching SEB_{ON})

During the SEB/SEGR testing, not a single input current event was observed, demonstrating that the TPS7H6003-SP is SEB/SEGR-free up to LET_{EFF} = 75 MeV × cm^2 / mg at a flux of approximately 10^5 ions / cm^2 × s, fluences of approximately 10^7 ions / cm^2, and a die temperature of ≈25°C.

The TPS7H6003-SP was characterized for SET with LET_{EFF} = 48 to 75 MeV × cm^2 / mg at flux ≈10^5 ions / cm^2 × s, fluence of ≈10^7 ions / cm^2, and a die temperature of 25°C. For SET the device operated at nominal operating conditions with a V_{IN} of 12 V and V_{BOOT} of 12 V with ASW at 150 V. The specific test conditions for the devices for SET are as follows:

PWM Mode:

- EN/HI:
- 5-V DC signal (SET)

PWM/LI:

- 5-V Square Wave switching at 500-kHz and 50% duty cycle (SET)

IIM Modes:

- Case 1 – EN/HI = 0-V, PWM/LI = 5-V (Static SET)
- Case 2 – EN/HI = 5-V, PWM/LI = 0-V (Static SET)
- Case 3 - EN/HI & PWM/LI = 5-V square wave switching at 500-kHz offset by 180° (Switching SET)

Under these conditions the device showed on SET signature which was self-recoverable without the need for external intervention in both PWM and IIM mode. In PWM mode and IIM_{SW} mode HO and LO were monitored to see if the output pulse width ever exceeded a 20 % trigger. In IIM_{ST} mode HO and LO were monitored to see if the signals triggered on either a positive or negative edge depending on whether HO or LO were forced high based on the input value on EN/HI and PWM/LI. In all cases transients lasted approximately 5 us before recovering back to normal operation. Transients are further discussed in the Single-Event Transients section. To see the SET results of the TPS7H6003-SP, see Single-Event Transients (SET).

3 Device and Test Board Information

The TPS7H6003-SP is packaged in a 48-pin ceramic package as shown in Figure 3-1. A TPS7H6003-SP evaluation board made specifically for radiation testing was used to evaluate the performance and characteristics of the TPS7H6003-SP under heavy ion radiation. The TPS7H6003-SP evaluation board is shown in Figure 3-2. The board schematic is shown in Figure 3-3.

The package was delidded to reveal the die face for all heavy-ion testing.

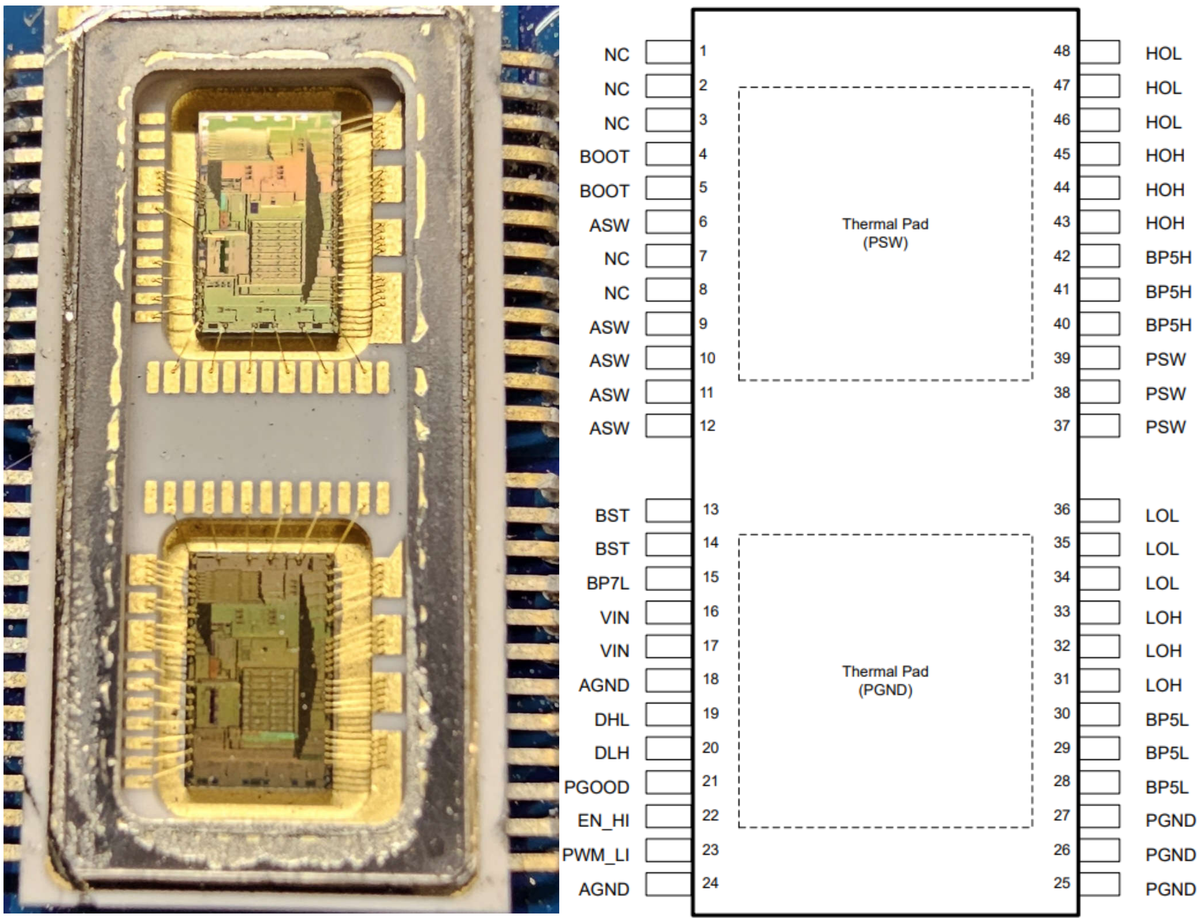

Figure 3-1. Photograph of Delidded TPS7H6003-SP [Left] and Pinout Diagram [Right]

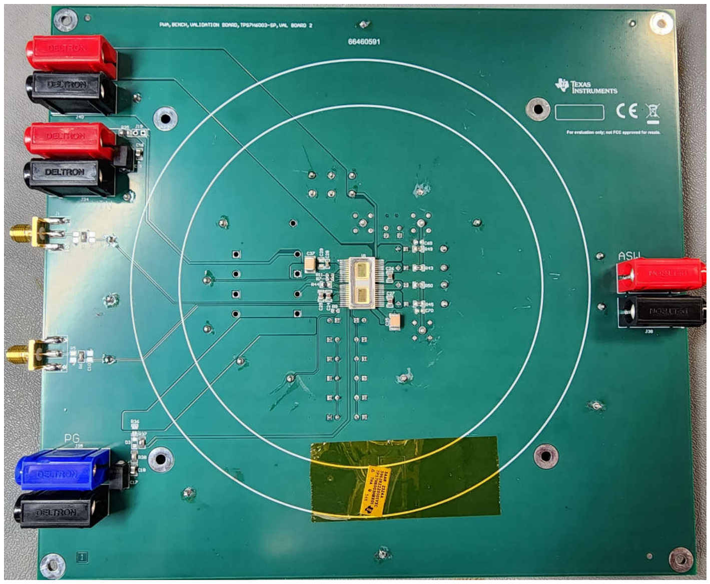

Figure 3-2. TPS7H6003-SP EVM Top View

Although not shown here, there are 1-nF capacitors on the HO and LO outputs. See the block diagram for the setup of the capacitive load.

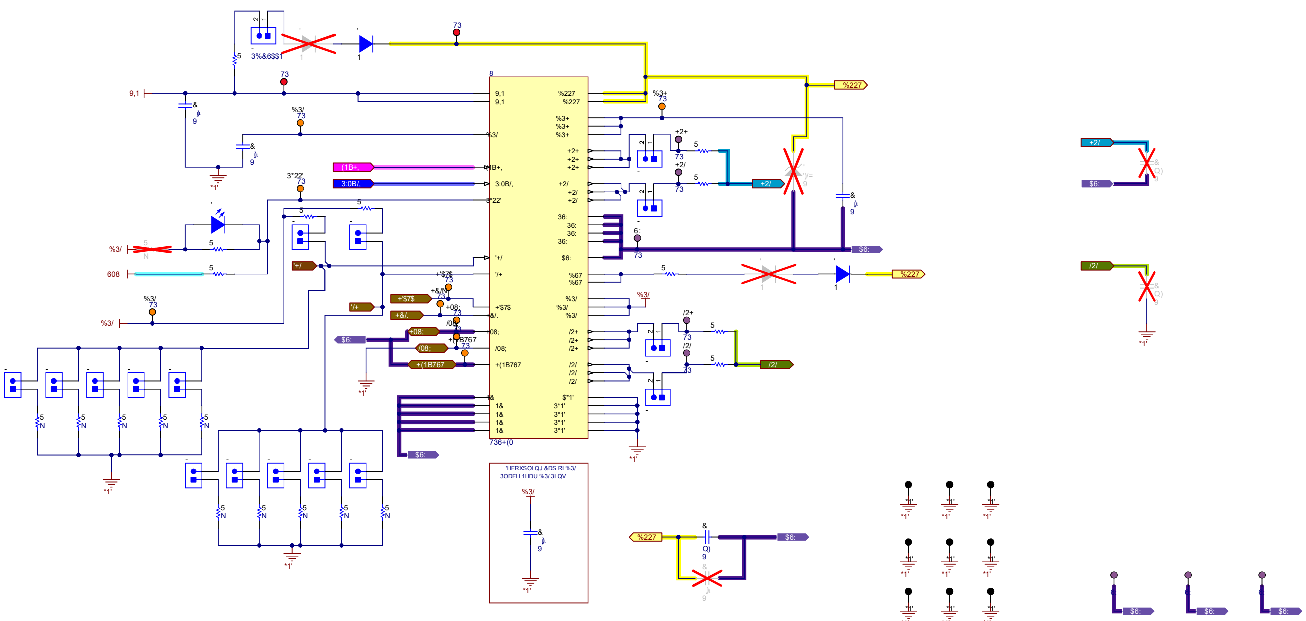

Figure 3-3. TPS7H6003-SP Evaluation Board Schematics

4 Irradiation Facility and Setup

The heavy-ion species used for the SEE studies on this product were provided and delivered by the TAMU Cyclotron Radiation Effects Facility using a superconducting cyclotron and an advanced electron cyclotron resonance (ECR) ion source. At the fluxes used, ion beams had good flux stability and high irradiation uniformity over a 1-in diameter circular cross-sectional area for the in-air station. Uniformity is achieved by magnetic defocusing. The flux of the beam is regulated over a broad range spanning several orders of magnitude. For these studies, ion flux of 1.02×10^4 to 1.12×10^5 ions / cm^2 × s were used to provide heavy-ion fluences of 9.97×10^6 to 1.00×10^7 ions / cm^2.

For the experiments conducted on this report, there were three ions used, ^{109}Ag, ^{141}Pr, and ^{165}Ho. ^{109}Ag was used to obtain LET_{EFF} of 48 MeV × cm^2 / mg. ^{141}Pr was used to obtain LET_{EFF} of 65 MeV × cm^2 / mg. ^{165}Ho was used to obtain LET_{EFF} of 75 MeV × cm^2 / mg. The total kinetic energies for each of the ions were:

- ^{109}Ag = 1.634 GeV (15 MeV/nucleon)
  - Ion uniformity for these experiments was 94%
- ^{141}Pr = 2.114 GeV (15 MeV / nucleon)
- – Ion uniformity for these experiments was between 86 and 94%
- ^{165}Ho = 2.474 GeV (15 MeV / nucleon)
  - Ion uniformity for these experiments was between 88 and 92%

Figure 4-1 shows the TPS7H6003-SP Evaluation Board used for the data collection at the TAMU facility. Although not visible in this photo, the beam port has a 1-mil Aramica window to allow in-air testing while maintaining the vacuum within the accelerator with only minor ion energy loss. The in-air gap between the device and the ion beam port window was maintained at 40 mm for all runs.

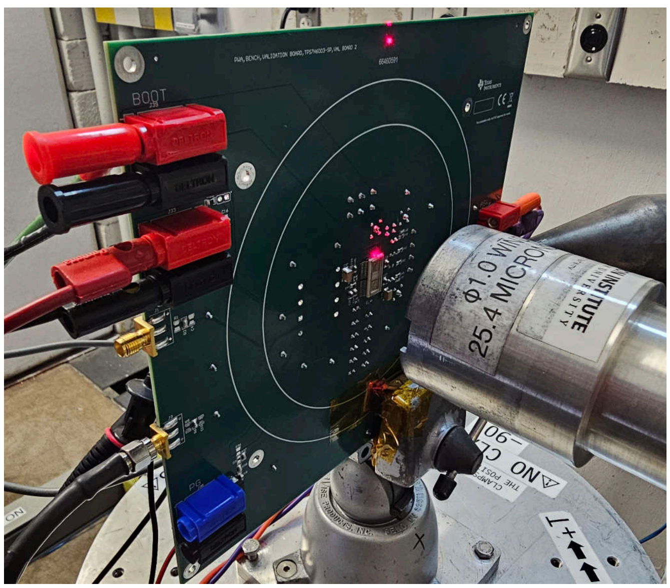

Figure 4-1. Photograph of the TPS7H6003-SP Evaluation Board in Front of the Heavy-Ion Beam Exit Port at the Texas A&M Cyclotron

5 Depth, Range, and LET$_{EFF}$ Calculation

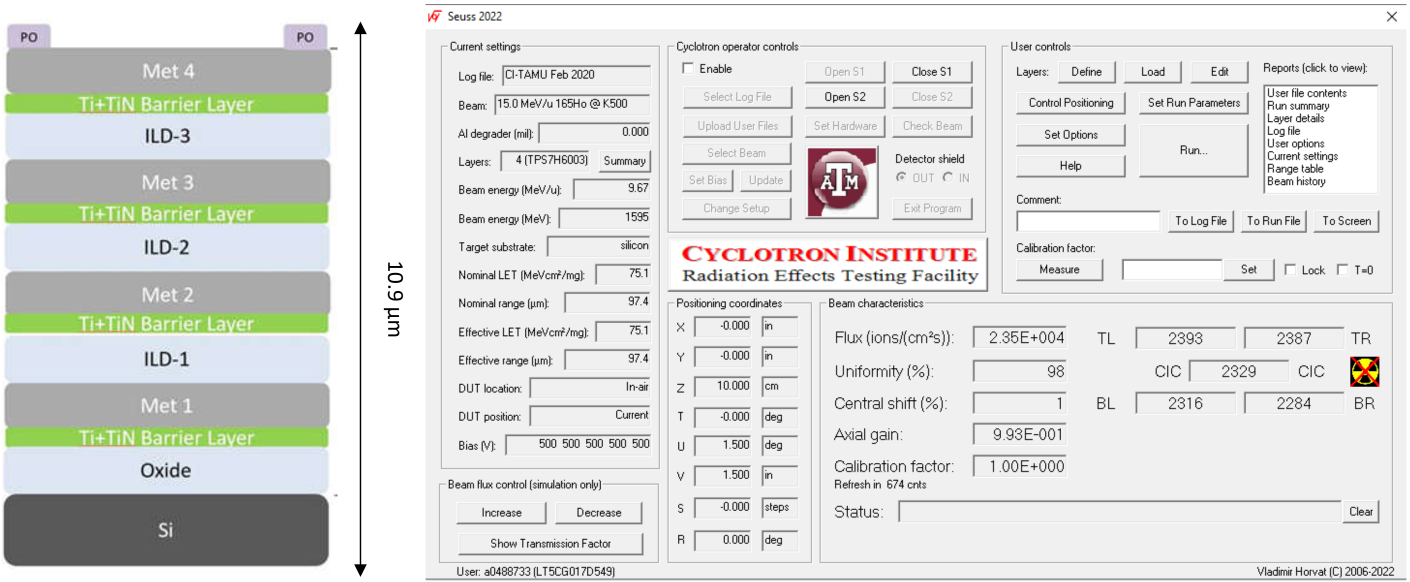

Figure 5-1. Generalized Cross-Section of the LBC7 Technology BEOL Stack on the TPS7H6003-SP (Left) and SEUSS 2020 Application Used to Determine Key Ion Parameters (Right)

The TPS7H6003-SP is fabricated in the TI Linear BiCMOS 250-nm process with a 4LM back-end-of-line (BEOL) stack. The total stack height from the surface of the passivation to the silicon surface is 9.8 µm based on nominal layer thickness as shown in Figure 5-1. Accounting for energy loss through the 1-mil thick Aramica beam port window, the 40-mm air gap, and the BEOL stack over the TPS7H6003-SP, the effective LET (LET$_{EFF}$) at the surface of the silicon substrate and the depth was determined with the SEUSS 2020 Software (provided by the Texas A&M Cyclotron Institute and based on the latest SRIM-2013 [7] models). The results are shown in Ion LET$_{EFF}$, Depth, and Range in Silicon.

Table 5-1. Ion LET$_{EFF}$, Depth, and Range in Silicon

Ion Type	Beam Energy (MeV / nucleon)	Angle of Incidence	Degrader Steps (Number)	Degrader Angle	Range in Silicon (µm)	LET$_{EFF}$ (MeV × cm^2/ mg)
^{109}Ag	15	0	0	0	95.1	48
^{141}Pr	15	0	0	0	100.8	65
^{165}Ho	15	0	0	0	97.2	75

6 Test Setup and Procedures

There were five input supplies used to power the TPS7H6003-SP which provided V_{IN}, V_{BOOT}, EN/HI, PWM/LI, and ASW (ASW with respect to AGND). The VIN for the device was provided via Ch. 3 of an N6705C power module and ranged from 12-V to 14-V for SET and DSEE respectively. The V_{BOOT} for the device was provided by Ch. 1 of an N6705C power module and ranged from 12-V to 14-V SET and DSEE respectively. EN/HI and PWM/LI were provided by a National Instruments PXIe-5433 2-channel AWG or a National Instruments PXIe-4139 depending on the type of test. Lastly, the ASW was provided by a National Instruments PXIe-4137 and forced to 150 V.

The primary signals monitored on the EVM were HO and LO and this was done so using two instruments. The first was a NI PXIe-5110 which triggered (based on HO) in two ways, Pulse-Width at 20% outside width in PWM or IIM_{SW} mode, and window (± 500-mV with signal AC coupled) in IIM_{ST} mode. The second instrument was a MSO58B oscilloscope which triggered in a similar manner for the LO signal while also monitoring the BP5L signal.

All equipment other than the MSO58B was controlled and monitored using a custom-developed LabVIEW™ program (PXI-RadTest) running on a HP-Z4® desktop computer. The computer communicates with the PXI chassis through an MXI controller and NI PXIe-8381 remote control module. The MSO58B was used using the manufacturer interface. The MSO was set to fast-frame for all SET data collection.

Equipment Settings and Parameters Used During the SEE Testing of the TPS7H6003-SP shows the connections, limits, and compliance values used during the testing. Figure 6-1 shows a block diagram of the setup used for SEE testing of the TPS7H6003-SP.

Table 6-1. Equipment Settings and Parameters Used During the SEE Testing of the TPS7H6003-SP

Pin Name	Equipment Used	Capability	Compliance	Range of Values Used
V_{IN}	N6705C (CH # 3)	20.4 V, 50 A	5 A	12 to 14 V
V_{BOOT}	N6705C (CH # 1)	60 V, 20 A	5 A	12 to 14 V
EN/HI	PXIe-5433 (CH # 0)	24 V_{PK-PK}, 80 MHz	—	5 V to 14 V, 500 kHz to 2 MHz
	PXI-4139	60 V, 3 A	3 A	14 V
PWM/LI	PXIe-5433 (CH # 1)	24 V_{PK-PK}, 80 MHz	—	5 V to 14 V, 500 kHz to 2 MHz
	PXI-4139	60 V, 3 A	3 A	14 V
LO, BP5L	MSO58B	6.25 GS / s	—	1 GS / s
HO	PXIe-5110	100 MS / s	—	100 MS / s

All boards used for SEE testing were fully checked for functionality. Dry runs were also performed to ensure that the test system was stable under all bias and load conditions prior to being taken to the TAMU facility. During the heavy-ion testing, the LabVIEW control program powered up the TPS7H6003-SP device and set the external sourcing and monitoring functions of the external equipment. After functionality and stability was confirmed, the beam shutter was opened to expose the device to the heavy-ion beam. The shutter remained open until the target fluence was achieved (determined by external detectors and counters). During irradiation, the NI scope cards continuously monitored the signals. When the output exceeded the pre-defined trigger, a data capture was initiated. No sudden increases in current were observed (outside of normal fluctuations) on any of the test runs and indicated that no SEL or SEB/SEGR events occurred during any of the tests.

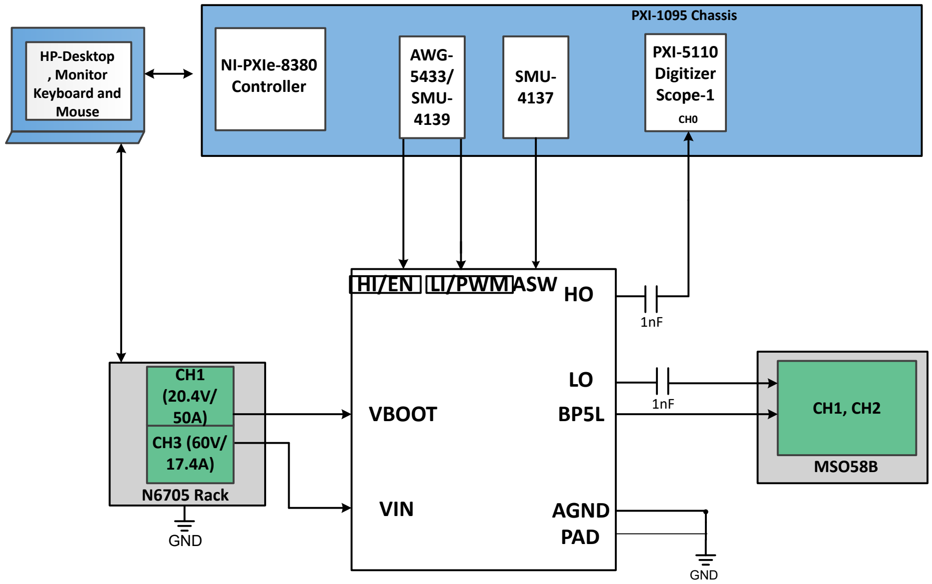

Figure 6-1. Block Diagram of the SEE Test Setup for the TPS7H6003-SP

7 Destructive Single-Event Effects (DSEE)

7.1 Single-Event Latch-up (SEL) Results

During the SEL testing the device was heated to 125°C by using a Closed-Loop PID controlled heat gun (MISTRAL 6 System (120V, 2400W)). The temperature of the die was verified using thermal camera prior to exposure to heavy ions.

The species used for the SEL testing was Homium (^{165}Ho at 15 MeV / nucleon). For the ^{165}Ho ion an angle of incedence of 0° was used to achieve an LET_{EFF} = 75 MeV × cm^2 / mg (for more details, see Ion LET_{EFF}, Depth, and Range in Silicon). The kinetic energy in the vacuum for this ions is 2.474 GeV. Flux of approximately 10^5 ions / cm^2× s and a fluence of approximately 10^7 ions / cm^2 per run was used. Run duration to achieve this fluence was approximately two minutes. The four devices were powered up and exposed to the heavy-ions using the maximum recommended input voltage and boot voltage of 14 V. The ASW (High-Side Driver Signal Return) was set to 150-V with respect to AGND (low-side driver signal return). The device was set in both PWM and IIM modes during testing, for more information please refer back to the Single-Event Effects section. No SEL events were observed during all nine runs, indicating that the TPS7H6003-SP is SEL-free up to 75 MeV·cm^2 / mg. Table 7-1 shows the SEL test conditions and results. Figure 7-1 shows a plot of the current versus time for run # 1.

Table 7-1. Summary of TPS7H6003-SP SEL Test Condition and Results

Run Number	Unit Number	Ion	LET_{EFF} (MeV × cm^2 / mg)	Flux (ions × cm^2 / mg)	Fluence (Number of ions)	V_{IN}	V_{BOOT}	Mode	EN/HI	PWM/LI	SEL (# Events)
1	1	^{165}Ho	75	6.22 × 10^4	1.00 × 10^7	14	14	PWM	14 V_{DC}	14 $V_{pk\text{-}pk}$ 500 kHz	0
2	1	^{165}Ho	75	6.26 × 10^5	9.99 × 10^6	14	14	PWM	14 V_{DC}	14 $V_{pk\text{-}pk}$ 1 MHz	0
3	1	^{165}Ho	75	6.19 × 10^4	9.99 × 10^6	14	14	PWM	14 V_{DC}	14 $V_{pk\text{-}pk}$ 2 MHz	0
4	2	^{165}Ho	75	6.23 × 10^4	1.00 x 10^7	14	14	IIM_{ENST}	14 V_{DC}	0 V	0
5	2	^{165}Ho	75	5.79 × 10^4	1.00 × 10^7	14	14	IIM_{ENST}	0 V	14 V_{DC}	0
6	3	^{165}Ho	75	7.46 × 10^4	1.00 × 10^7	14	14	IIM_{ENSW}	14 $V_{pk\text{-}pk}$ 500 kHz	14 $V_{pk\text{-}pk}$ 500 kHz	0
7	3	^{165}Ho	75	6.88 × 10^4	1.00 × 10^7	14	14	IIM_{DISSW}	14 $V_{pk\text{-}pk}$ 500 kHz	14 $V_{pk\text{-}pk}$ 500 kHz	0
8	4	^{165}Ho	75	5.64 × 10^4	1.00 × 10^7	14	14	IIM_{DISST}	14 V_{DC}	0 V	0
9	4	^{165}Ho	75	5.78 × 10^4	1.00 × 10^7	14	14	IIM_{DISST}	0 V	14 V_{DC}	0

Using the MFTF method described in *Single-Event Effects (SEE) Confidence Interval Calculations* and combining (or summing) the fluences of the four runs at 125°C (4 × 10^7), the upper-bound cross-section (using a 95% confidence level) is calculated as:

$$\sigma_{SEL} \leq 4.11\ x\ 10^{-8}\ cm^2/device\ for\ LET_{EFF}\ =\ 75\ MeV \cdot cm^2/mg\ and\ T\ =\ 125°C$$

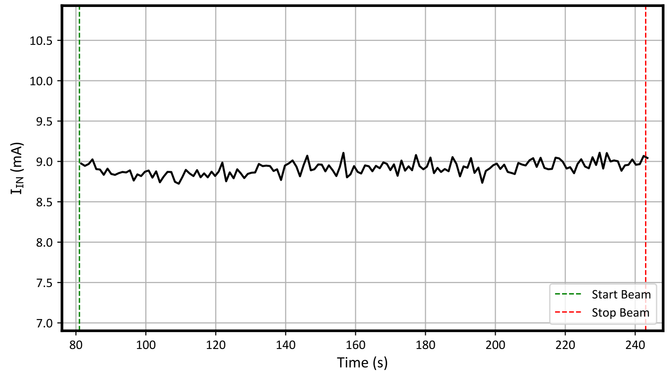

Figure 7-1. SEL Run #1 (PWM Mode, f_{sw} = 500 kHz)

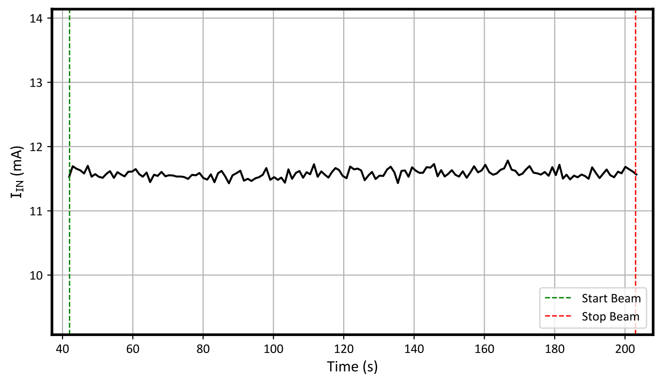

Figure 7-2. SEL Run #2 (PWM Mode, f_{sw} = 1 MHz)

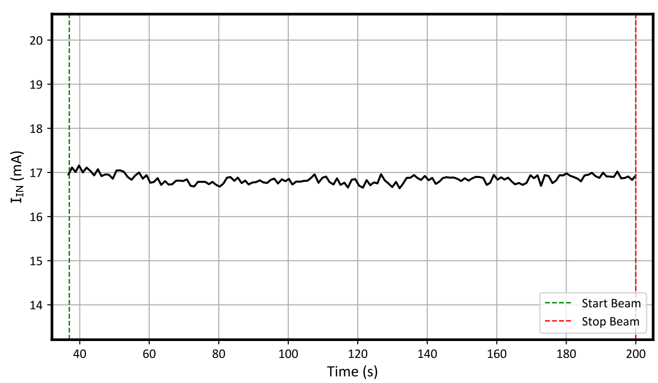

Figure 7-3. SEL Run #3 (PWM Mode, f_{sw} = 2 MHz)

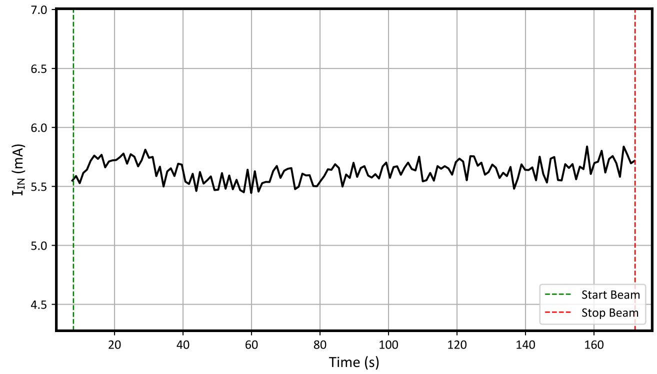

Figure 7-4. SEL Run #4 (IIM Enabled Mode, PWM/LI = 14 V)

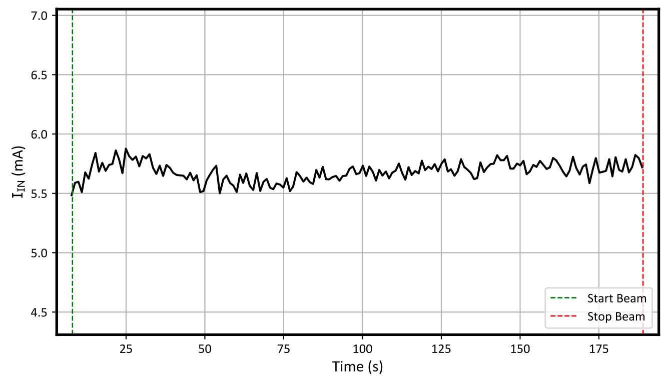

Figure 7-5. SEL Run #9 (IIM Disabled Mode, EN/HI = 14 V)

7.2 Single-Event Burnout (SEB) and Single-Event Gate Rupture (SEGR) Results

During the SEB/SEGR characterization, the device was tested at room temperature of approximately 25°C. The device was tested under both the enabled and disabled mode. For the SEB-OFF mode the device was disabled using the EN-pin by forcing 0 V while in PWM mode and by holding both inputs low during the IIM mode testing. During the SEB/SEGR testing with the device enabled or disabled, not a single input current event was observed.

The species used for the SEB testing was Homium (^{165}Ho at 15 MeV / nucleon). For the ^{165}Ho ion an angle of incidence of 0° was used to achieve an LET_{EFF} = 75 MeV × cm^2 / mg (for more details, see Ion LET_{EFF}, Depth, and Range in Silicon). The kinetic energy in the vacuum for this ion is 2.474 GeV (15-MeV / amu line). Flux of approximately 10^5 ions / cm^2 × s and a fluence of approximately 10^7 ions / cm^2 was used for the run. Run duration to achieve this fluence was approximately two minutes. The four devices (same as used in SEL testing) were powered up and exposed to the heavy-ions using the maximum recommended input voltage and boot voltage of 14 V. The ASW (High-Side Driver Signal Return) was set to 150 V. The device was set in both PWM and IIM modes during testing. For more information, see Single-Event Effects section. No SEB/SEGR current events were observed during the 12 runs, indicating that the TPS7H6003-SP is SEB/SEGR-free up to LET_{EFF} = 75 MeV × cm^2/ mg and across the full electrical specifications. Summary of TPS7H6003-SP SEB/SEGR Test Condition and Results shows the SEB/SEGR test conditions and results.

Table 7-2. Summary of TPS7H6003-SP SEB/SEGR Test Condition and Results

Run Number	Unit Number	Ion	LET_{EFF} (MeV × cm^2 / mg)	Flux (ions × cm^2/ mg)	Fluence (number of ions)	Enabled Status	V_{IN}	V_{BOOT}	Mode	Switching Frequency	SEB Event?
10	1	^{165}Ho	75	6.11 × 10^4	9.98 × 10^6	EN	14	14	PWM	500 kHz	No
11	1	^{165}Ho	75	6.59 × 10^4	1.00 × 10^7	EN	14	14	PWM	1 MHz	No
12	1	^{165}Ho	75	6.50 × 10^4	1.00 × 10^7	EN	14	14	PWM	2 MHz	No
13	1	^{165}Ho	75	6.44 × 10^4	1.00 × 10^7	DIS	14	14	PWM	N/A	No
14	2	^{165}Ho	75	6.09 × 10^4	1.00 × 10^7	EN	14	14	IIM_{ENST}	N/A	No
15	2	^{165}Ho	75	6.14 × 10^4	1.00 × 10^7	EN	14	14	IIM_{ENST}	N/A	No
16	2	^{165}Ho	75	6.26 × 10^4	1.00 × 10^7	DIS	14	14	IIM_{ENST}	N/A	No
17	2	^{165}Ho	75	6.49 × 10^4	9.99 × 10^6	DIS	14	14	IIM_{DISST}	N/A	No
18	3	^{165}Ho	75	8.27 × 10^4	1.00 × 10^7	EN	14	14	IIM_{ENSW}	500 kHz	No
19	3	^{165}Ho	75	7.25 × 10^4	1.00 × 10^7	EN	14	14	IIM_{DISSW}	500 kHz	No
20	4	^{165}Ho	75	5.68 × 10^4	1.00 × 10^7	EN	14	14	IIM_{DISST}	N/A	No
21	4	^{165}Ho	75	6.03 × 10^4	1.00 × 10^7	EN8	14	14	IIM_{DISST}	N/A	No

Using the MFTF method described in *Single-Event Effects (SEE) Confidence Interval Calculations*, the upper-bound cross-section (using a 95% confidence level) is calculated as:

$$\sigma_{SEB} \leq 3.08 \, x \, 10^{-8} \, cm^2/device \; for \; LET_{EFF} = 75 \, MeV \cdot cm^2/mg \; and \; T = 25°C \quad (1)$$

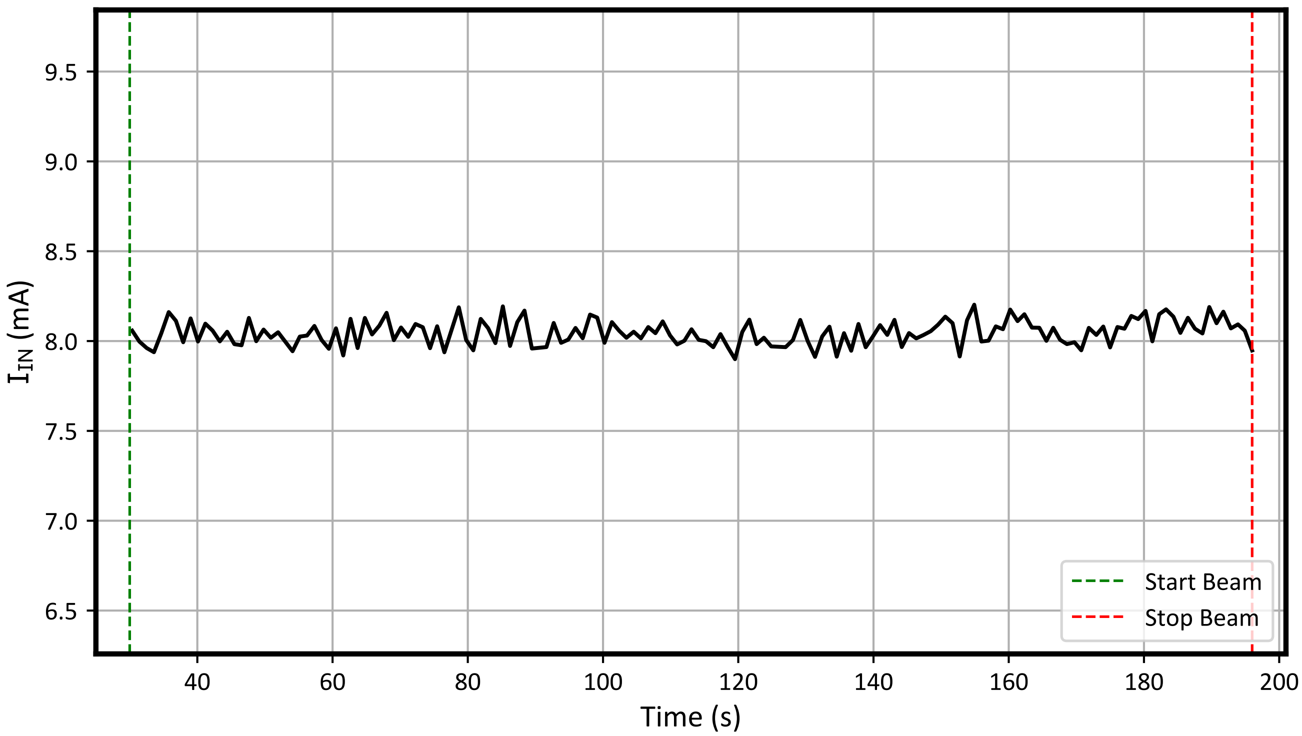

Figure 7-6. SEB On Run 10 (PWM Mode, f_{sw}= 500 kHz)

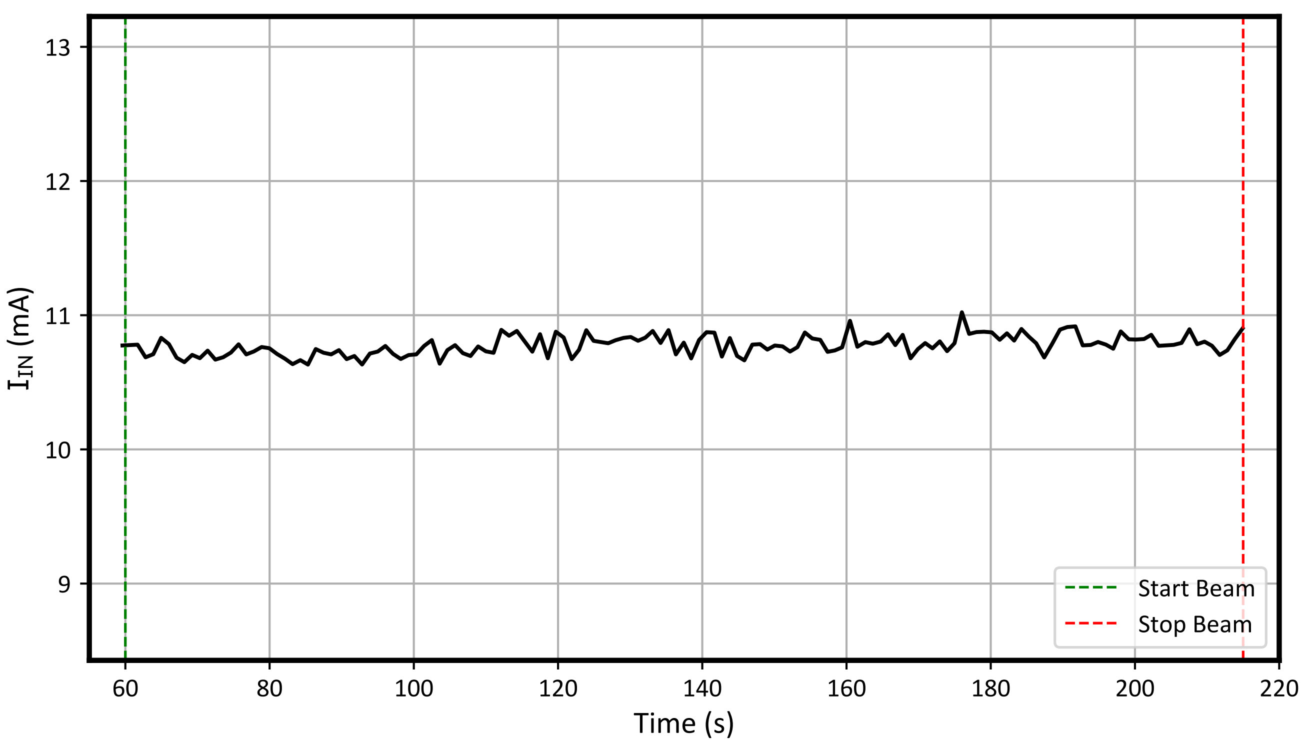

Figure 7-7. SEB On Run 11 (PWM Mode, f_{sw} = 1 MHz)

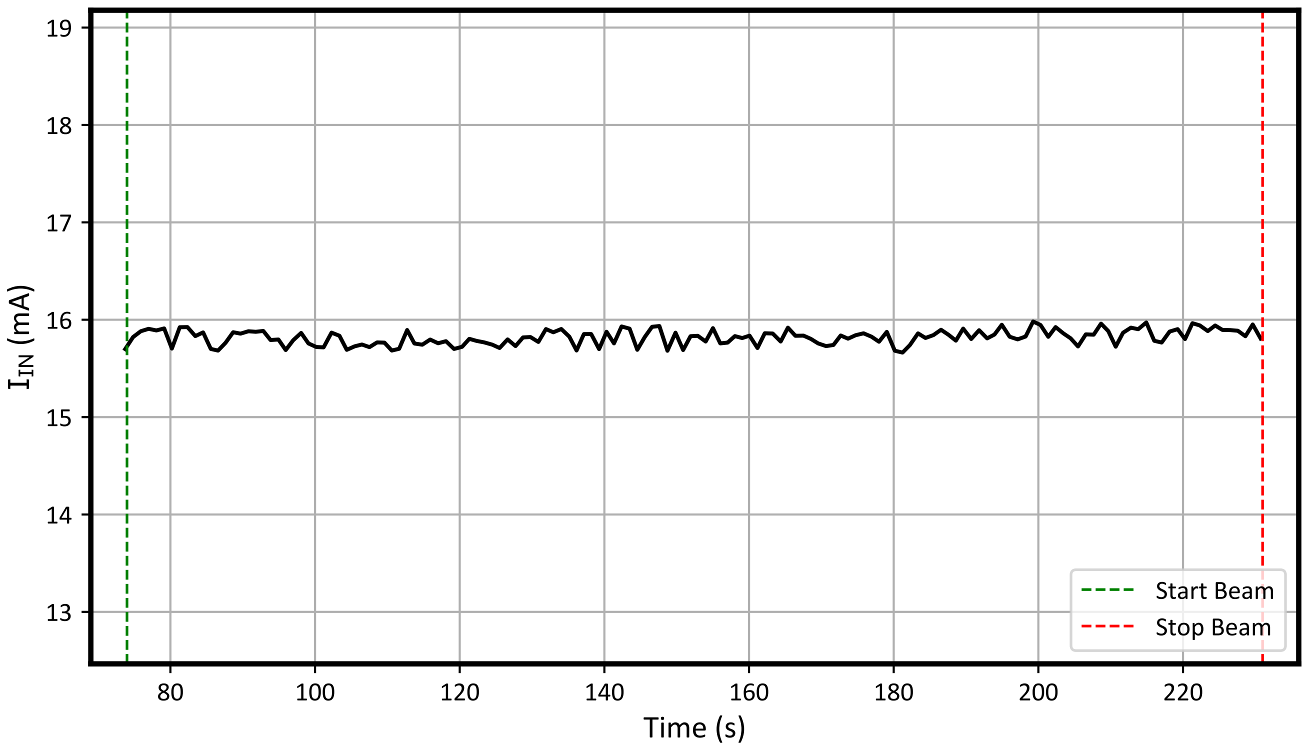

Figure 7-8. SEB On Run 12 (PWM Mode, f_{sw}= 2 MHz)

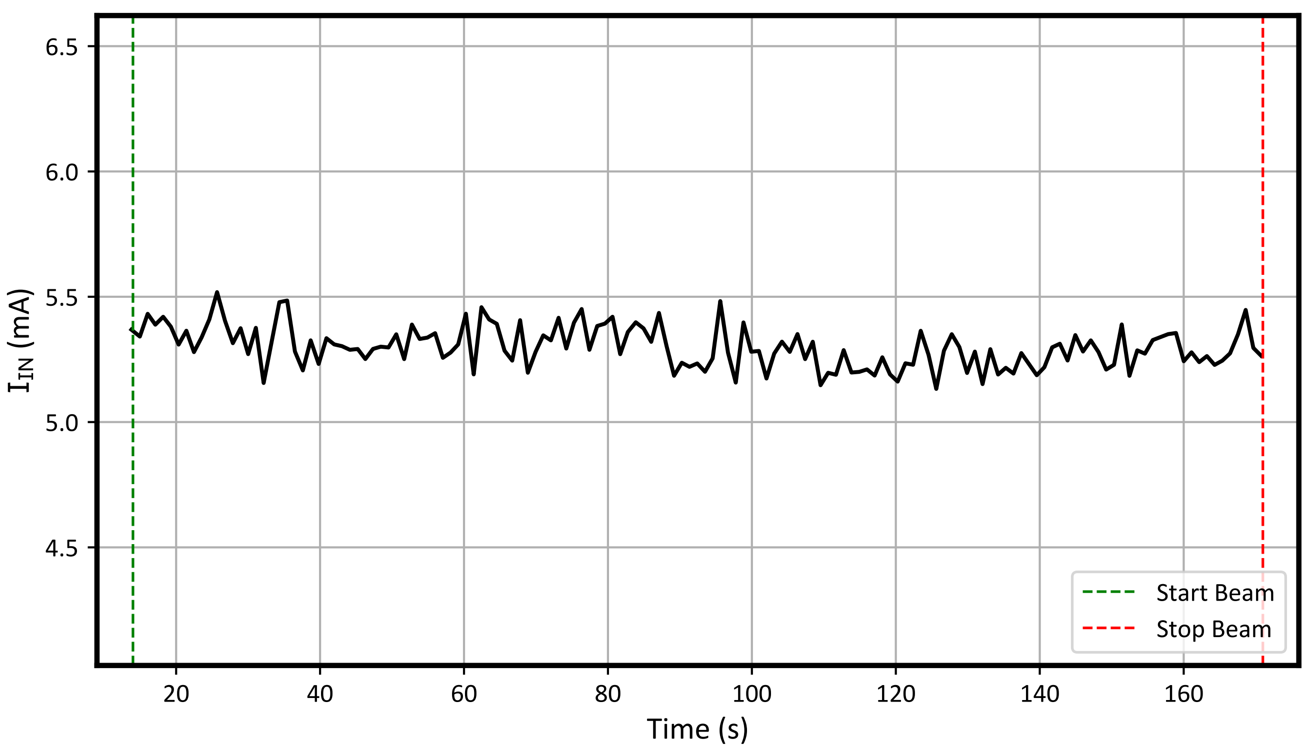

Figure 7-9. SEB Off Run 13 (PWM Mode)

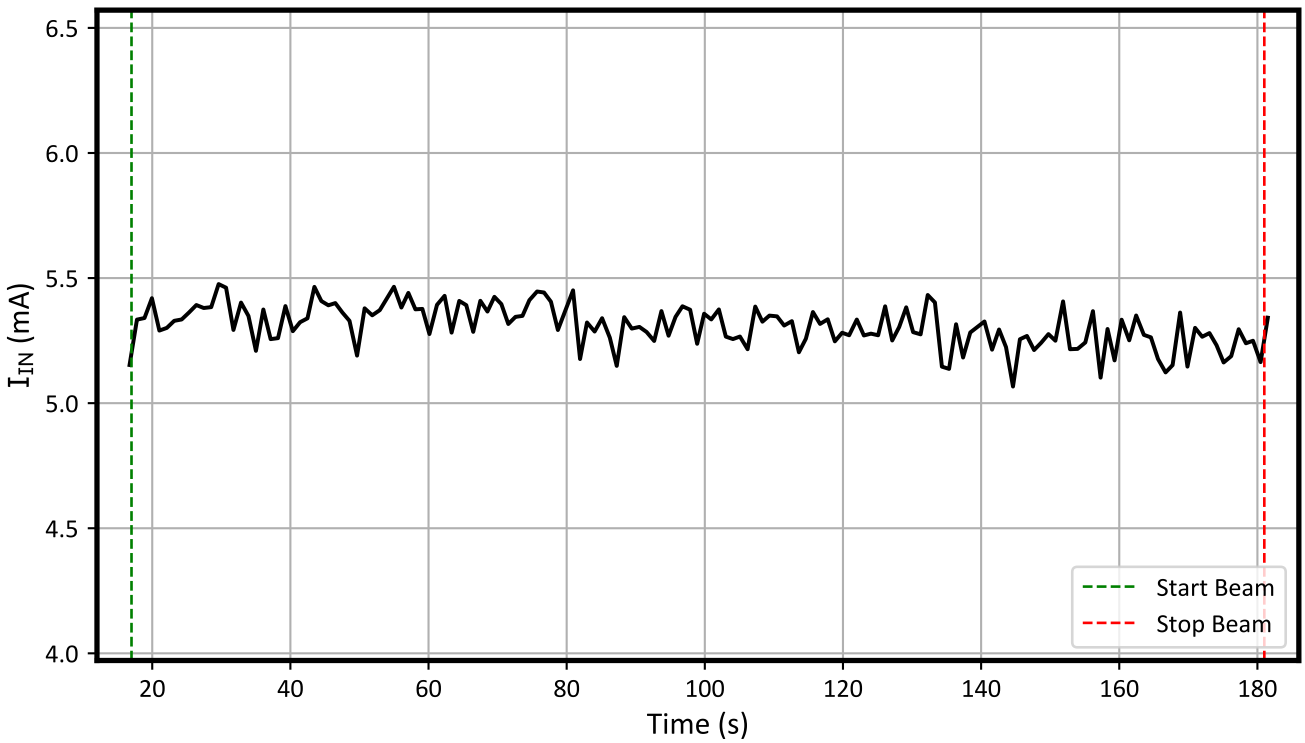

Figure 7-10. SEB On Run 14 (IIM-Enabled Mode, EN/HI = 14 V)

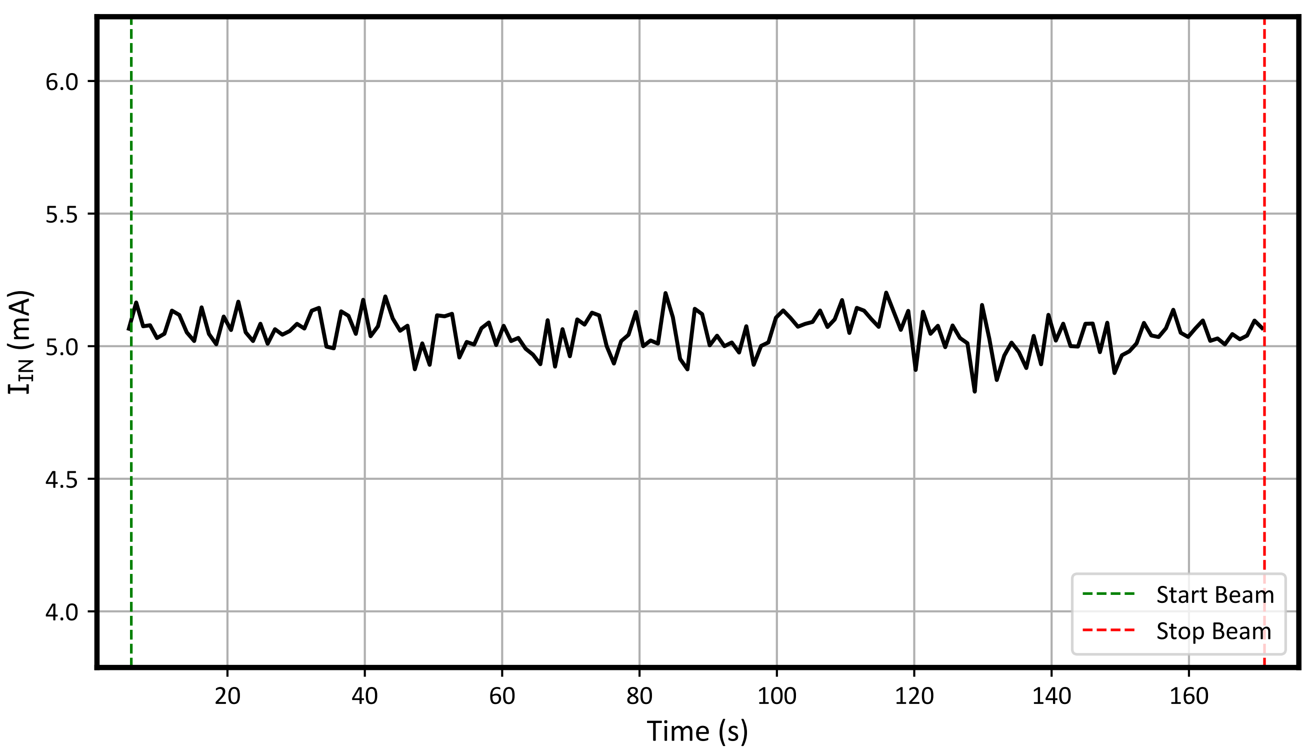

Figure 7-11. SEB Off Run 16 (IIM-Enabled Mode)

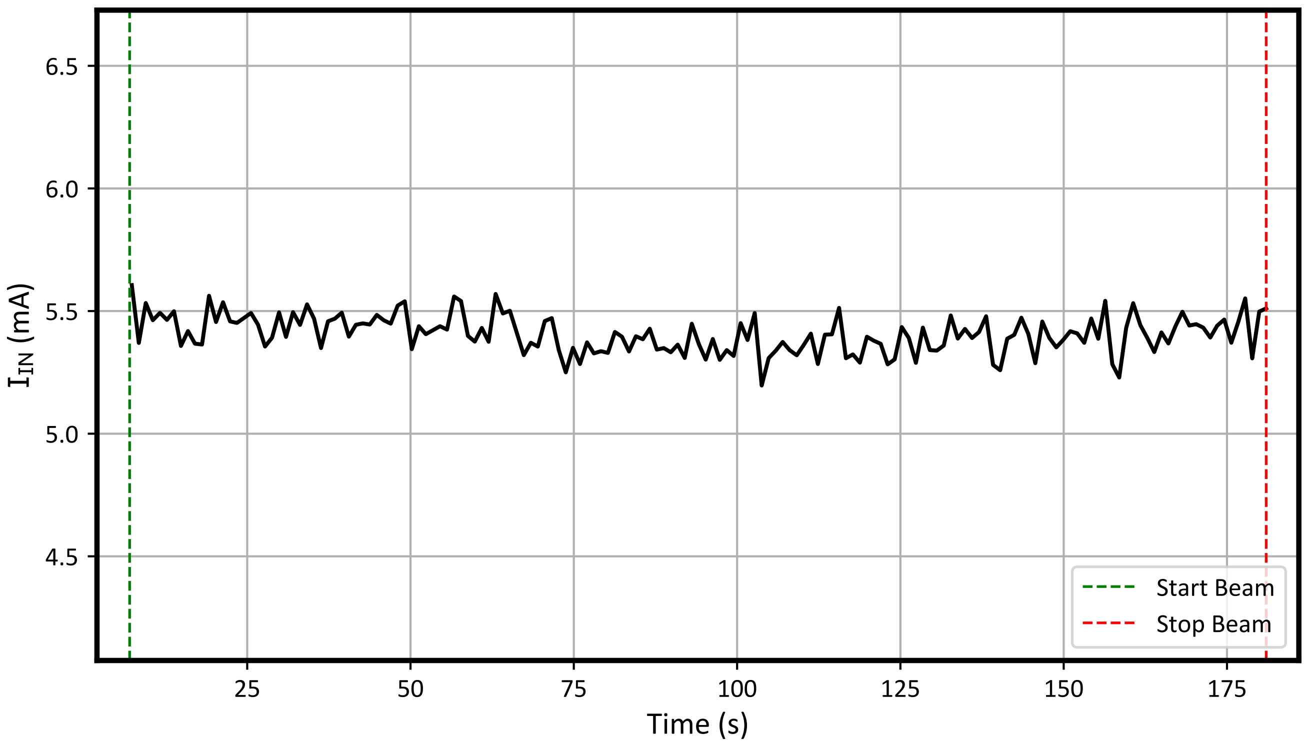

Figure 7-12. SEB On Run 21 (IIM-Disabled Mode, PWM/LI = 14 V)

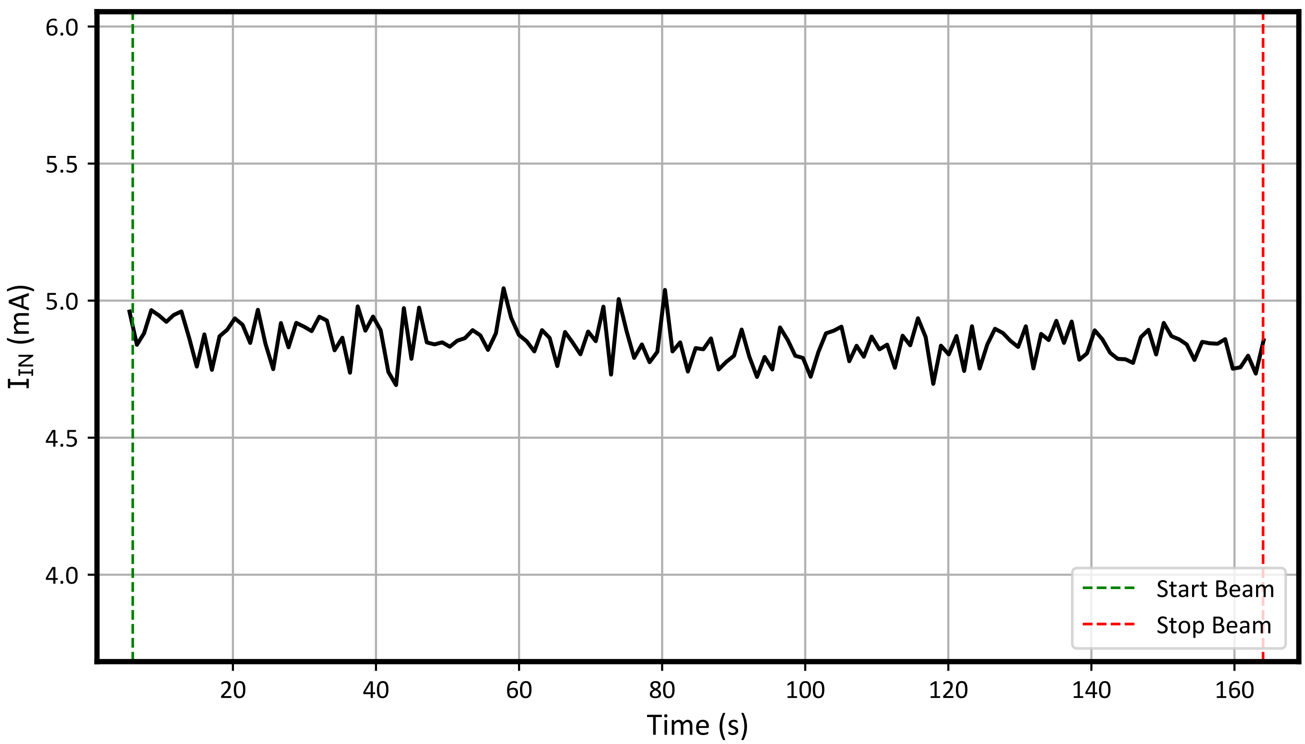

Figure 7-13. SEB Off Run 17 (IIM-Disabled Mode)

8 Single-Event Transients (SET)

The primary focus of SETs were heavy-ion-induced transient upsets on the output signals HO and LO (with a 1-nF capacitive load on the outputs as seen in block diagram). SET testing was done at room temperature across three ion species, ^{109}Ag, ^{141}Pr, and ^{165}Ho which produced a range of LET_{EFF} of 48 to 75 MeV × cm^2 / mg for more details, see Ion LET_{EFF}, Depth, and Range in Silicon. HO and LO were monitored by two different scopes, a NI PXIe-5110 and a MSO58B oscilloscope. During PWM and IIM_{SW} mode testing, each scope was configured to trigger based on an “outside” pulse width measurement, where the window for the output signal was 20% (±200ns). During the IIM_{ST} modes, the same two scopes were used, however, the trigger was a window which was 500-mV above or 500-mV below 0-V with the signals AC-coupled. The signals in this mode were monitored to see if the signal ever went low when it should have been high, or high when it should have been low. During all SET testing, there was NO cross-conduction in either PWM or IIM mode and in IIM mode the only transient that occurred was a high to low transient, no signals ever “turned on” when they weren't supposed to. For all recorded transients, there were never cases where the pulse deviated to be greater than 20%. The only captured SETs were missed pulses. During the IIM mode testing with LO high and during the PWM mode testing during a LO transient, the signature of the transient shows that there is some overshoot (approximately 410 mV during static and approximately 480 mV during switching) before leveling back out to 5 V during the turn on. This is consistent across all transients, but all signals do recover back to nominal after the overshoot in the order of µs. Because of this BP5L was monitored on the MSO58B in order to show that this overshoot is from the internal LDO.

Waveform size, sample rate, trigger type, value, and signal for all scopes used is listed in Table 8-1.

Table 8-1. Scope Settings

Note: Only one signal was used as a trigger source at a time, this table just present all posible sources for a given scope, the same is valid for the trigger type. All percentage specified on the trigger value are deviation from the nominal value.

Scope Model	Trigger Signal	Trigger Type	Trigger Value	Record Length	Sample Rate
MSO58B	LO	Pulse Width/Window	± 20% / ±500 mV	20 µs / div	250 MS / s
	BP5L	N/A	N/A		
PXIe-5110	HO	Pulse Width/Window	± 20% / ±500-mV	20k	100 MS / s

Table 8-2. Summary of TPS7H6003-SP SET Test Condition and Results

Run Number	Unit Number	Ion	LET_{EFF} (MeV × cm^2 / mg)	Flux (ions × cm^2/ mg)	Fluence (number of ions)	Mode	MSO58B LO Number	PXIe-5110 HO Number
22	1	^{165}Ho	75	6.33×10^4	1.00×10^7	PWM	7	5
23	3	^{165}Ho	75	8.12×10^4	1.00×10^7	IIM_{ENSW}	5	6
24	3	^{165}Ho	75	7.14×10^4	1.00×10^7	IIM_{DISSW}	2	2
25	4	^{165}Ho	75	6.87×10^4	1.00×10^7	IIM_{DISST}	0	4
26	4	^{165}Ho	75	6.50×10^4	1.00×10^7	IIM_{DISST}	4	0
27	1	^{141}Pr	65	1.13×10^5	9.99×10^6	PWM	1	3
28	3	^{141}Pr	65	1.09×10^5	1.00×10^7	IIM_{DISST}	2	0
29	3	^{141}Pr	65	1.07×10^5	1.00×10^7	IIM_{DISST}	0	1
30	4	^{141}Pr	65	1.11×10^5	1.00×10^7	IIM_{DISSW}	0	0
31	4	^{141}Pr	65	1.28×10^5	1.00×10^7	IIM_{ENSW}	0	1
32	1	^{109}Ag	48	9.79×10^4	1.00×10^7	PWM	0	0
33	3	^{109}Ag	48	1.00×10^5	1.00×10^7	IIM_{DISST}	0	0
34	3	^{109}Ag	48	1.00×10^5	1.00×10^7	IIM_{DISST}	0	0

Upper and lower bound cross-sections were calculated to 95% confidence. Weibull fit was done to calculate the onset value.

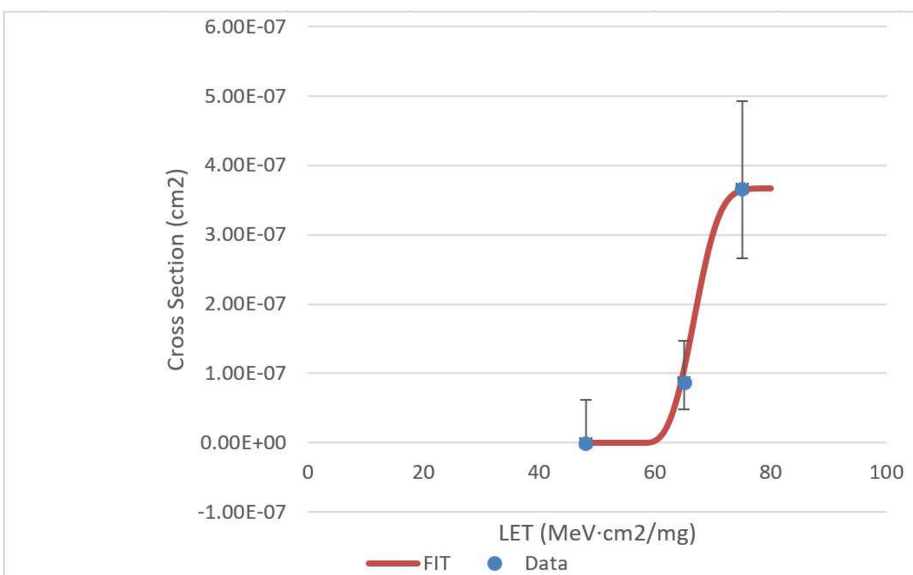

Figure 8-1. Cross Section and Weibull Fit for HO and LO SET Test Cases

A Weibull fit was conducted to determine the best estimation of onset since there were transients at 65 MeV, but none at 48 MeV. Because of the gap between LET levels there is high probability that the true onset is somewhere between the two tested levels. Based on this fit the estimated true onset for the TPS7H6003-SP is 58 MeV.

Table 8-3. Weibull Parameters for HO and LO SET Test Cases

Parameter	Units
Upper Bound Cross-Section (cm^2)	4.87×10^{-7}
Cross-Saturation (cm^2)	3.50×10^{-7}
Onset (MeV-cm^2/mg)	58
w	10
s	3

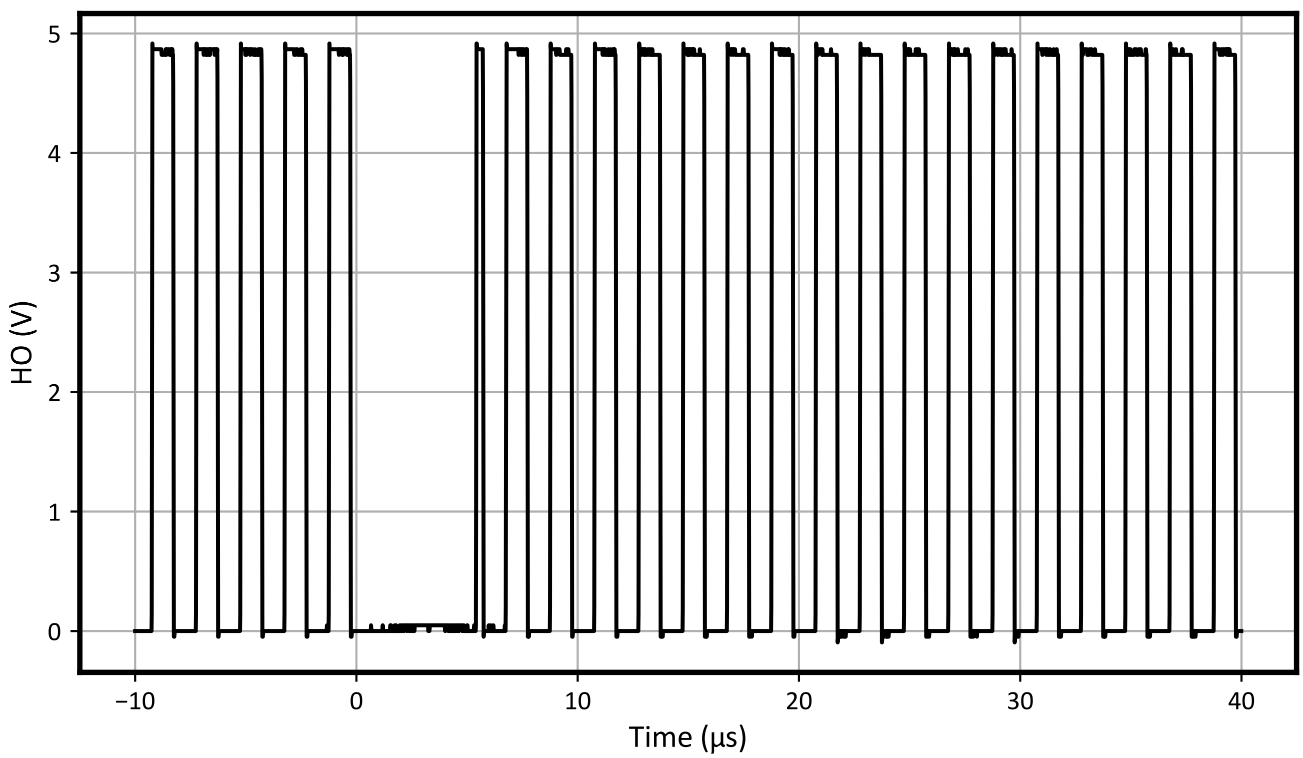

Figure 8-2. HO SET Run 22 (PWM Mode, f_{sw} = 500 kHz)

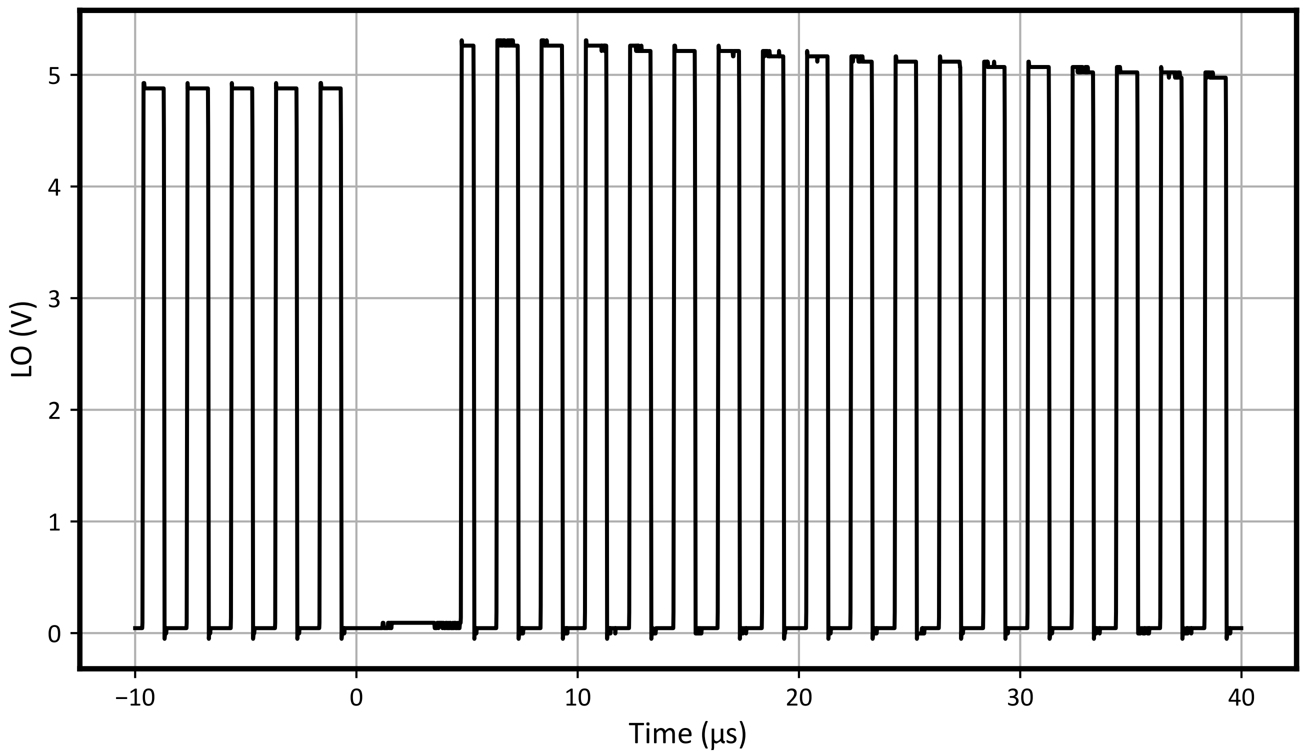

Figure 8-3. LO SET Run 22 (PWM Mode, f_{sw} = 500 kHz)

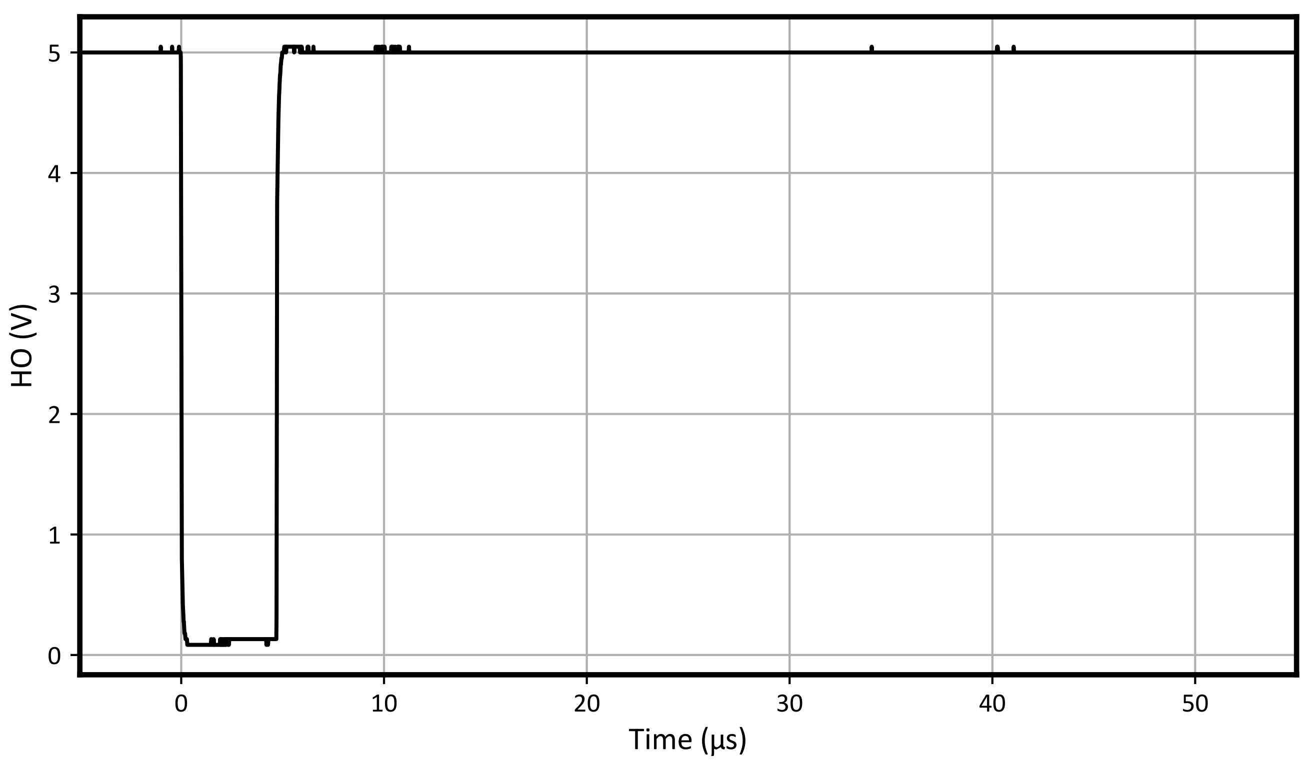

Figure 8-4. HO SET Run 25 (IIM-Disabled Mode, EN/HI = 5 V)

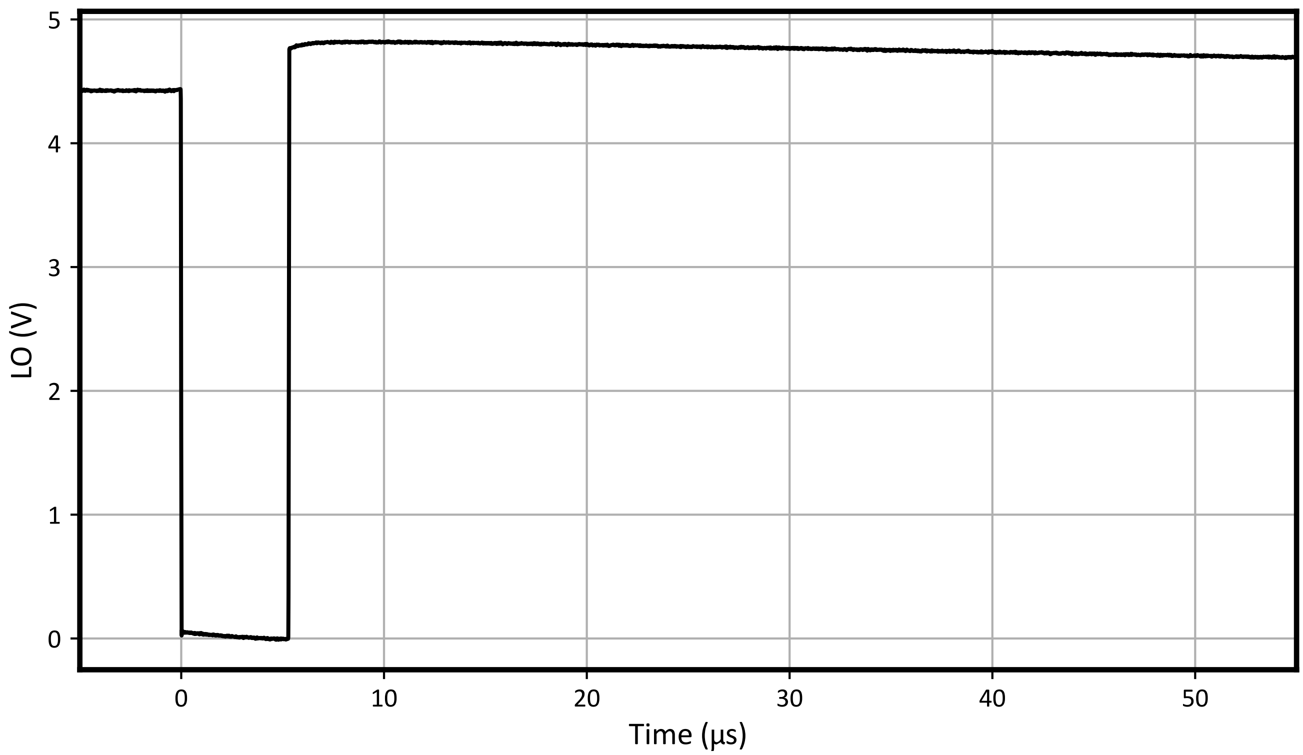

Figure 8-5. LO SET Run 26 (IIM-Disabled Mode, PWM/LI = 5 V)

9 Event Rate Calculations

Event rates were calculated for LEO (ISS) and GEO environments by combining CREME96 orbital integral flux estimations and simplified SEE cross-sections according to methods described in *Heavy Ion Orbital Environment Single-Event Effects Estimations*. We assume a minimum shielding configuration of 100 mils (2.54 mm) of aluminum, and “worst-week” solar activity (this is similar to a 99% upper bound for the environment). Using the 95% upper-bounds for the SEL and the SEB/SEGR, the event rate calculation for the SEL and the SEB/SEGR is shown on Table 9-1 and Table 9-2, respectively. **It is important to note that this number is for reference since no SEL or SEB/SEGR events were observed.** SET orbit rate is presented onSEB/SEGR Event Rate Calculations for Worst-Week LEO and GEO Orbits.

Table 9-1. SEL Event Rate Calculations for Worst-Week LEO and GEO Orbits

Orbit Type	Onset LET_{EFF} (MeV-cm²/mg)	CREME96 Integral FLUX (/day/cm²)	σSAT (cm²)	Event Rate (/day)	Event Rate (FIT)	MTBE (Years)
LEO (ISS)	75	6.26×10^{-5}	4.11×10^{-8}	2.57×10^{-12}	1.07×10^{-4}	1.07×10^{9}
GEO		1.77×10^{-4}		7.26×10^{-12}	3.03×10^{-4}	3.77×10^{8}

Table 9-2. SEB/SEGR Event Rate Calculations for Worst-Week LEO and GEO Orbits

Orbit Type	Onset LET_{EFF} (MeV-cm²/mg)	CREME96 Integral FLUX (/day/cm²)	σSAT (cm²)	Event Rate (/day)	Event Rate (FIT)	MTBE (Years)
LEO (ISS)	75	6.26×10^{-5}	3.08×10^{-8}	1.93×10^{-12}	8.04×10^{-5}	1.42×10^{9}
GEO		1.77×10^{-4}		5.45×10^{-12}	2.27×10^{-4}	5.03×10^{8}

Table 9-3. SET Event Rate Calculations for Worst-Week LEO and GEO Orbits

Orbit Type	Onset LET_{EFF} (MeV-cm²/ mg)	CREME96 Integral FLUX (/ day / cm²)	σSAT (cm²)	Event Rate (/ day)	Event Rate (FIT)	MTBE (Years)
LEO (ISS)	58	2.02×10^{-4}	4.87×10^{-7}	9.84×10^{-11}	4.10×10^{-3}	2.78×10^{7}
GEO		6.14×10^{-4}		2.99×10^{-10}	1.24×10^{-2}	9.17×10^{6}

10 Summary

The purpose of this study was to characterize the effect of heavy-ion irradiation on the single-event effect (SEE) performance of the TPS7H6003-SP 200-V half-bridge eGaN gate driver. Heavy-ions with LET_{EFF} = 48 to 75 MeV × cm^2 / mg were used for the SEE characterization campaign. Flux of approximately 10^5 ions / cm^2 × s and fluences of ≈10^7 ions/cm^2 per run were used for the characterization. The SEE results demonstrated that the TPS7H6003-SP is free of destructive SEL and SEB LET_{EFF} = 75 MeV × cm^2 / mg and across the full electrical specifications. Transients at LET_{EFF} = 48 to 75 MeV × cm^2 / mg on V_{OUT} are presented and discussed. CREME96-based worstweek event-rate calculations for LEO(ISS) and GEO orbits for the DSEE and SET are presented for reference.

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